



STU9HN65M2 Information



For Reference Only

Part Number STU9HN65M2

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 650V 5.5A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STU9HN65M2 Specifications

Manufacturer Part Number STU9HN65M2 Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series MDmesh? M2 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 5.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 11.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 325PF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 820 mOhm @ 2.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series MDmesh? M2 FET Type N-Channel Technology MOSFET (Metal Oxide) Parin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 11.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 325pF @ 100V Vgs (Max) FET Feature -Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 0perating Temperature 150°C (TJ) Mounting Type Supplier Device Package 1-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Manufacturer Part Number	STU9HN65M2
Package TO-251-3 Short Leads, IPak, TO-251AA Series MDmesh? M2 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 5.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 11.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 325pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 820 mOhm @ 2.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Manufacturer	STMicroelectronics
PackageTO-251-3 Short Leads, IPak, TO-251AASeriesMDmesh? M2FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C5.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs11.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds325pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)60W (Tc)Rds On (Max) @ Id, Vgs820 mOhm @ 2.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Category	Discrete Semiconductor Products
Series MDmesh? M2 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 5.5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 11.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 325pF @ 100V Vgs (Max) ±25V FET Feature Power Dissipation (Max) 60W (Tc) Rds On (Max) @ Id, Vgs 820 mOhm @ 2.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case Toother with the supplier Device Pack, IPak, TO-251AA		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Supplier Device Package Package / Case N-Channel Above 650V 5.5A (Tc) 10V 4V @ 250μA 11.5nC @ 10V 325pF @ 100V 425V FET Feature - Power Dissipation (Max) Bay mohm @ 2.5A, 10V Operating Temperature I50°C (TJ) Mounting Type Through Hole 1-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Package	TO-251-3 Short Leads, IPak, TO-251AA
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Vds	Series	MDmesh? M2
Drain to Source Voltage (Vdss)650 VCurrent - Continuous Drain (Id) @ 25°C5.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs11.5nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds325pF @ 100 VVgs (Max)±25 VFET Feature-Power Dissipation (Max)60W (Tc)Rds On (Max) @ Id, Vgs820 mOhm @ 2.5A, 10 VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Ygs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 5.5A (Tc) 60V 4V @ 250µA 610V 625V FET Feature - Power Dissipation (Max) 820 mOhm @ 2.5A, 10V Through Hole Supplier Device Package I-Pak TO-251-3 Short Leads, IPak, TO-251AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs11.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds325pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)60W (Tc)Rds On (Max) @ Id, Vgs820 mOhm @ 2.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case AV @ 250µA 4V @ 250µA 11.5nC @ 10V 325pF @ 100V 425V FET Ge 10V 60W (Tc) 820 mOhm @ 2.5A, 10V 150°C (TJ) Through Hole 150°C (TJ) Through Hole	Current - Continuous Drain (Id) @ 25°C	5.5A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +25V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 820 mOhm @ 2.5A, 10V Operating Temperature Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) #25V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 820 mOhm @ 2.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)60W (Tc)Rds On (Max) @ Id, Vgs820 mOhm @ 2.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	11.5nC @ 10V
FET Feature - GOW (Tc) Rds On (Max) @ Id, Vgs 820 mOhm @ 2.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	325pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 820 mOhm @ 2.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs 820 mOhm @ 2.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	60W (Tc)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	820 mOhm @ 2.5A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	150°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

STU9HN65M2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STU9HN65M2 Payment Methods





















STU9HN65M2 Shipping Methods













If you have any question about STU9HN65M2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com